



N-Channel Enhanced MOSFET

➤ **Features**

VDS	VGS	R _{DS(on)} Typ.	ID
100V	±20V	8.3mR@10V	56A
		11mR@4.5V	

➤ **Description**

This device is N-Channel enhancement MOSFET. Uses SGT technology and design to provide excellent R_{DS(on)} with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit.

➤ **Applications**

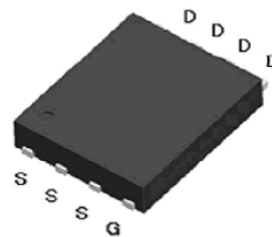
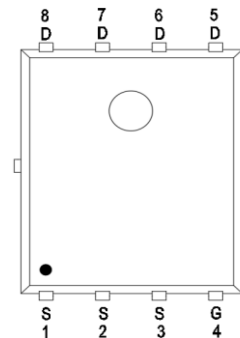
- DC/DC converters
- Power supplies
- Motor Drive Control
- Synchronous rectification

➤ **Ordering Information**

Device	Package	Shipping
SSC8LA0GN6	PDFN5X6	5000/Reel

➤ **Pin configuration**

Top view



PDFN5X6



Marking

(XX: product year / YY: product week)

➤ **Absolute Maximum Ratings**($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain-to-Source Voltage	100	V
V_{GSS}	Gate-to-Source Voltage	± 20	V
I_D	Continuous Drain Current ^d	$T_C=25^\circ\text{C}$	56
		$T_C=100^\circ\text{C}$	24
I_{DSM}	Continuous Drain Current ^a	$T_A=25^\circ\text{C}$	20
		$T_A=70^\circ\text{C}$	13
I_{DM}	Pulsed Drain Current ^b	220	A
P_D	Power Dissipation ^c	$T_C=25^\circ\text{C}$	46
		$T_C=100^\circ\text{C}$	18.5
P_{DSM}	Power Dissipation ^a	$T_A=25^\circ\text{C}$	5.4
		$T_A=70^\circ\text{C}$	3.5
I_{AS}	Avalanche Current ^b $L=0.5\text{mH}$ Single Pulse	9	A
E_{AS}	Avalanche Energy ^b $L=0.5\text{mH}$ Single Pulse	20	mJ
T_J	Operation junction temperature	-55~150	$^\circ\text{C}$
T_{STG}	Storage temperature range	-55~150	

➤ **Thermal Resistance Ratings**($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ^a	23	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	2.7	

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user is specific board design. The power dissipation is based on the $t \leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_D is based on $T_{J(\text{MAX})}=150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.
- The maximum current rating is package limited.

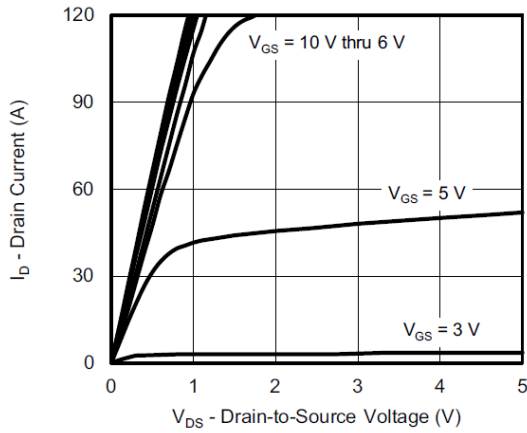


➤ **Electronics Characteristics**($T_A=25^{\circ}\text{C}$ unless otherwise noted)

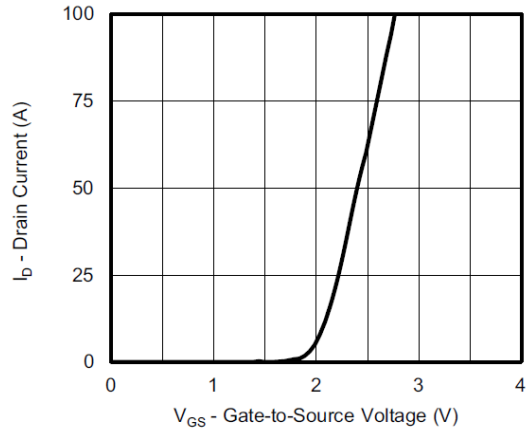
Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.3	1.7	2.3	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=20A$		8.3	10.5	mR
		$V_{GS}=4.5V, I_D=10A$		11	15	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=100V, V_{GS}=0V$			1	μA
I_{GSS}	Gate-Source leak current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
G_{FS}	Transconductance	$V_{DS}=5V, I_D=20A$		31		S
V_{SD}	Forward Voltage	$V_{GS}=0V, I_S=10A$		0.8	1.3	V
R_g	Gate Resistance	$V_{DS}=0V, f=1MHz$		1.8		R
C_{iss}	Input Capacitance	$V_{DS}=50V, V_{GS}=0V, f=1MHz$		2050		pF
C_{oss}	Output Capacitance			570		
C_{rss}	Reverse Capacitance			75		
$T_{D(ON)}$	Turn-on delay time	$V_{GS}=10V, R_L=2.5R$ $V_{DS}=50V, R_G=3R$		11		ns
T_r	Rise time			5		
$T_{D(OFF)}$	Turn-off delay time			22		
T_f	Fall time			7		
Q_G	Total Gate Charge	$V_{GS}=10V, V_{DS}=50V$ $I_D=20A$		28		nC
Q_{GS}	Gate Source Charge			14		
Q_{GD}	Gate Drain Charge			7		
T_{rr}	Diode Recovery Time	$I_F=20A, di/dt=500A/\mu s$		38		ns
Q_{rr}	Diode Recovery Charge	$I_F=20A, di/dt=500A/\mu s$		182		nC



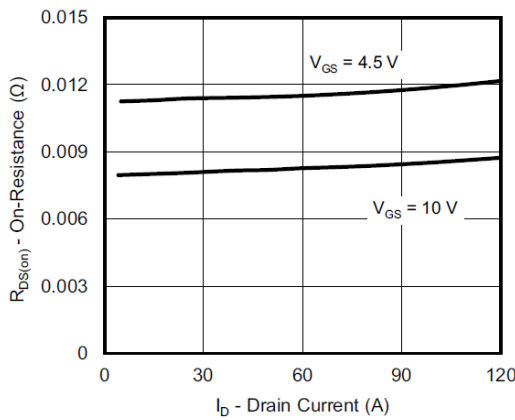
➤ **Typical Characteristics** ($T_A=25^\circ\text{C}$ unless otherwise noted)



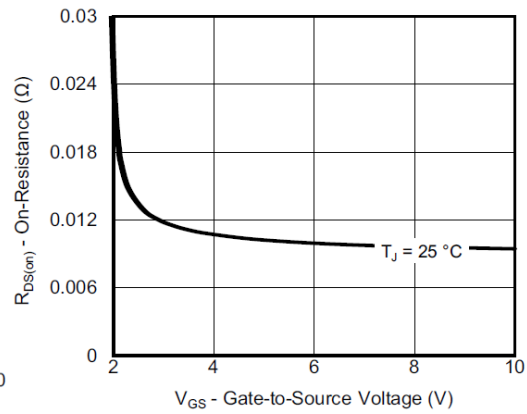
Output Characteristics



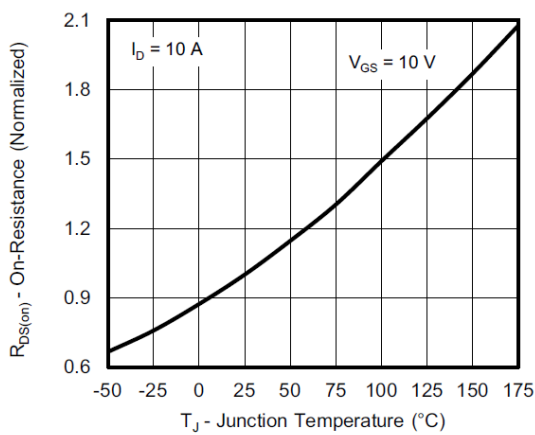
Transfer Characteristics



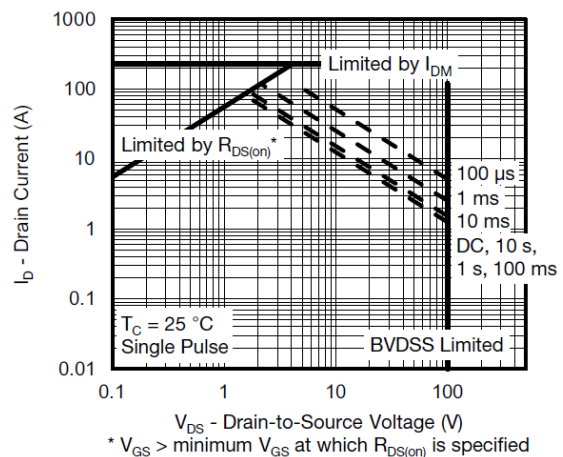
On-Resistance vs. Drain Current



On-Resistance vs. Gate-to-Source Voltage

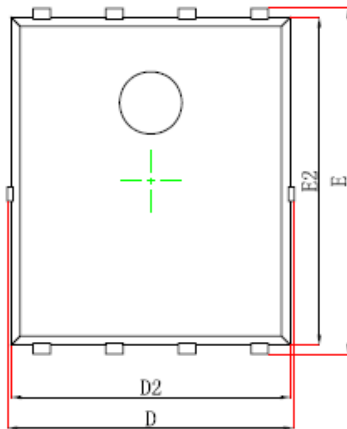


On-Resistance vs. Junction Temperature

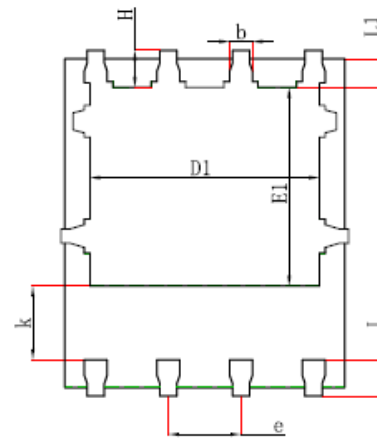


Safe Operating Area

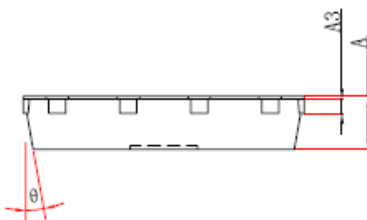
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

➤ Package Information


Top View
[顶视图]



Bottom View
[背视图]



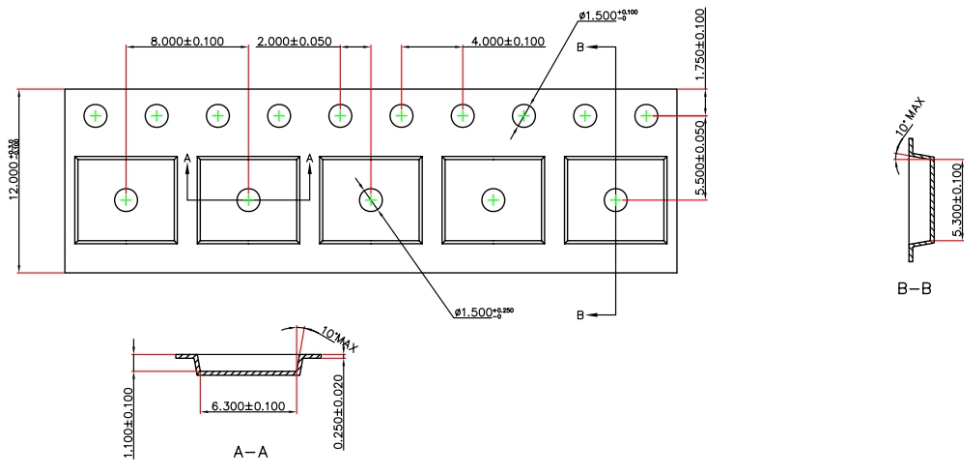
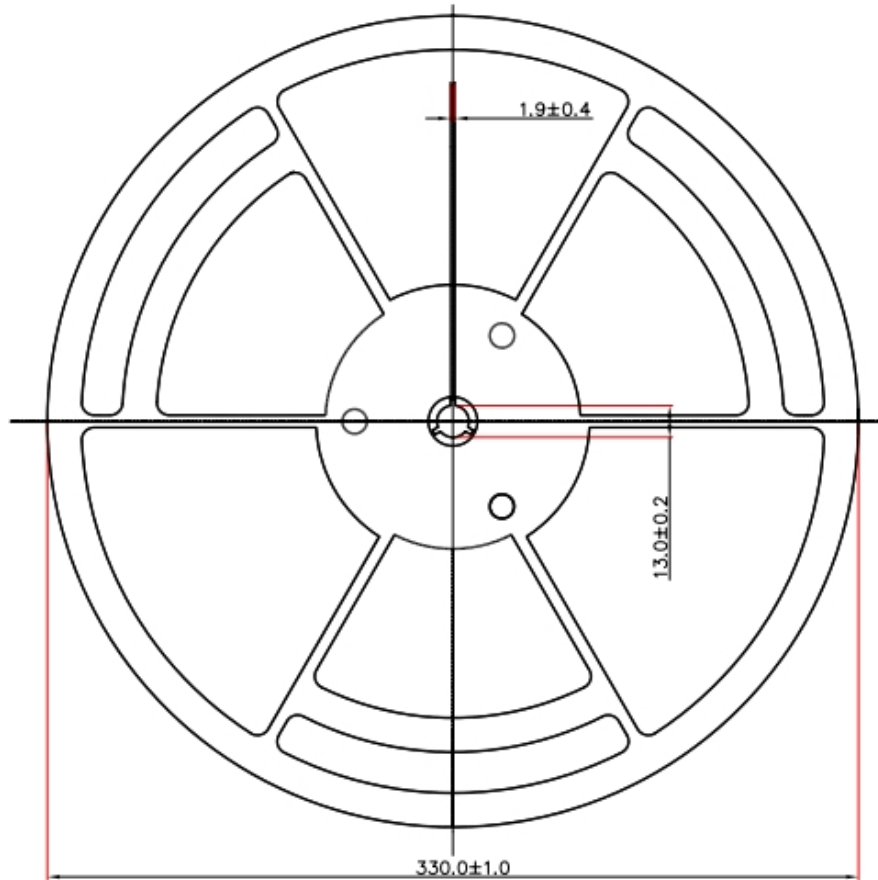
Side View
[侧视图]

Package: PDNF5X6-8L

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF		0.010REF	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP		0.050TYP	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°



➤ Tape and Reel





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